

SuperMOS – SOT-723 20V BV_{DSS} , 200m Ω $R_{DS(ON)}$, N-channel MOSFET

1. Description

The ES3134KR is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ES3134KR is Pb-free.

2. Features

- 20V, $R_{DS(ON)}=200m\Omega(Typ.) @ V_{GS}=4.5V$
- $R_{DS(ON)}=290m\Omega(Typ.) @V_{GS}=2.5V$
- $R_{DS(ON)}=480m\Omega(Typ.) @V_{GS}=1.8V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

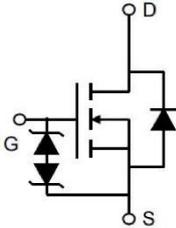
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ES3134KR	SOT-723	34KR	Halogen free	Tape & Reel	8,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	$T_A=25^\circ C$	0.7
		$T_A=75^\circ C$	0.54
Maximum Power Dissipation	P_D	0.22	W
Pulsed Drain Current	I_{DM}	2.8	A
Operating Junction Temperature	T_J	150	$^\circ C$
Lead Temperature	T_L	260	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

Thermal resistance ratings

Single Operation					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient Thermal Resistance	$t \leq 10s$ $R_{\theta JA}$		556	$^\circ C/W$	

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.35	0.75	1.10	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.5A$		200	300	m Ω
		$V_{GS}=2.5V, I_D=0.4A$		290	400	
		$V_{GS}=1.8V, I_D=0.2A$		480	700	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz,$ $V_{DS}=10V$		56		pF
Output Capacitance	C_{OSS}			20		
Reverse Transfer Capacitance	C_{RSS}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A$		1		nC
Gate-to-Source Charge	Q_{GS}			0.28		
Gate-to-Drain Charge	Q_{GD}			0.22		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A, R_G=10\Omega$		2		ns
Rise Time	t_r			18.8		
Turn-Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			23		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.5A$			1.5	V

7. Typical Characteristic

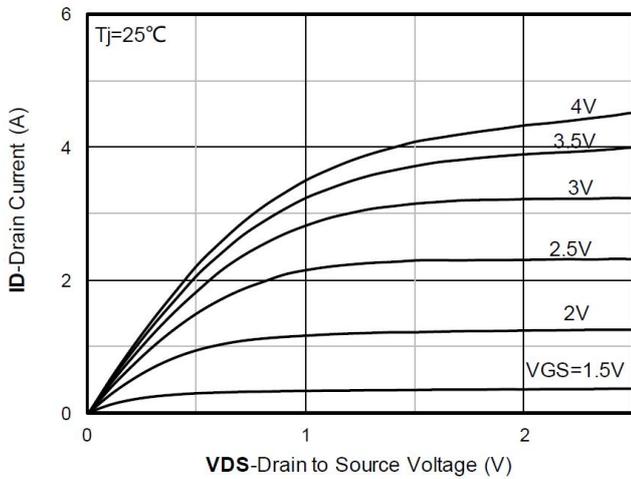


Figure1. Output Characteristics

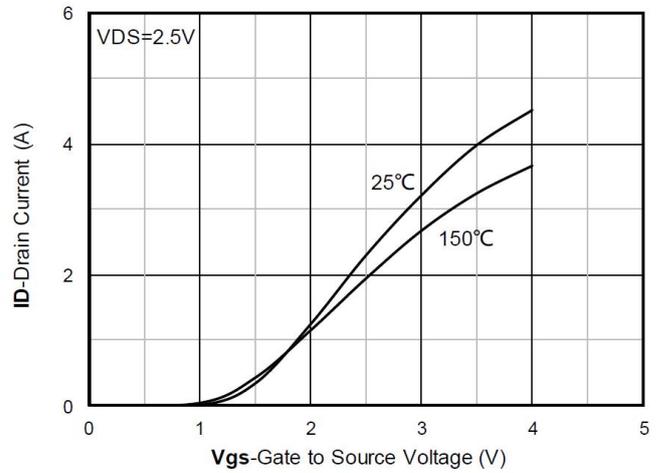


Figure2. Transfer Characteristics

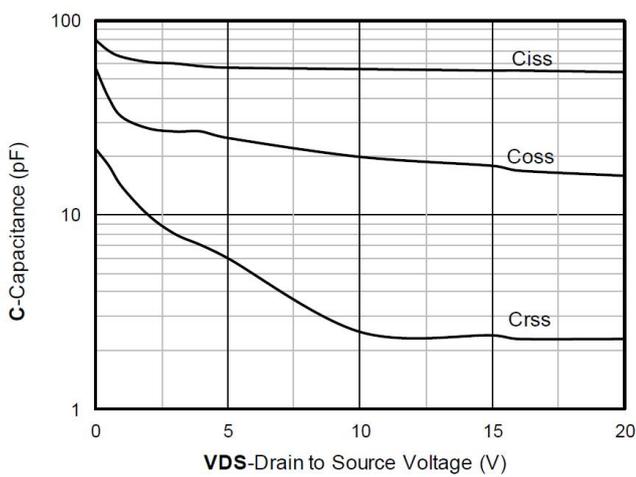


Figure3. Capacitance Characteristics

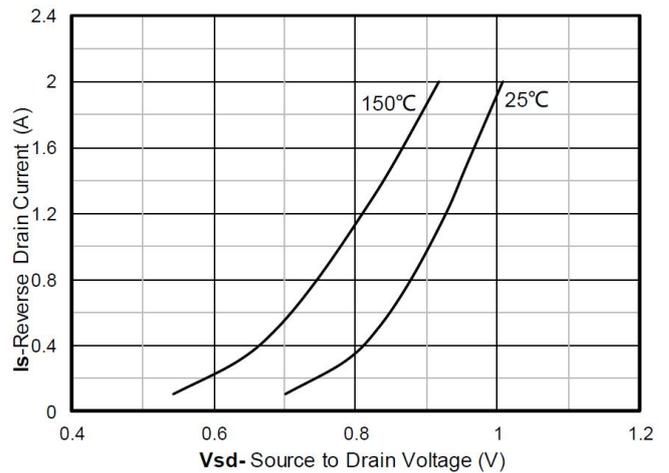


Figure4. Forward characteristics of reverse diode

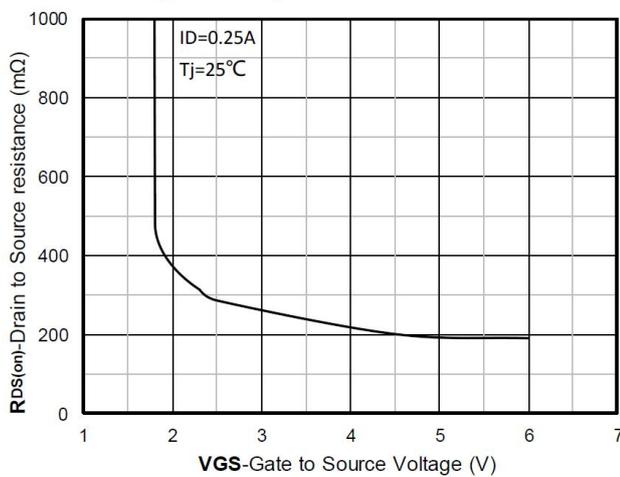


Figure5. On-Resistance vs Gate to Source Voltage

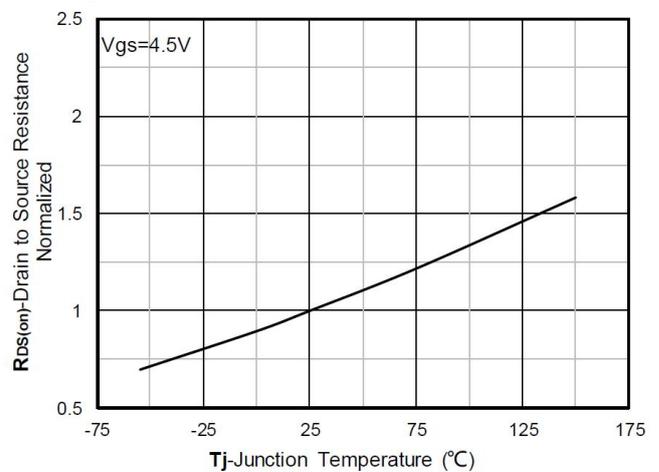


Figure6. Normalized On-Resistance

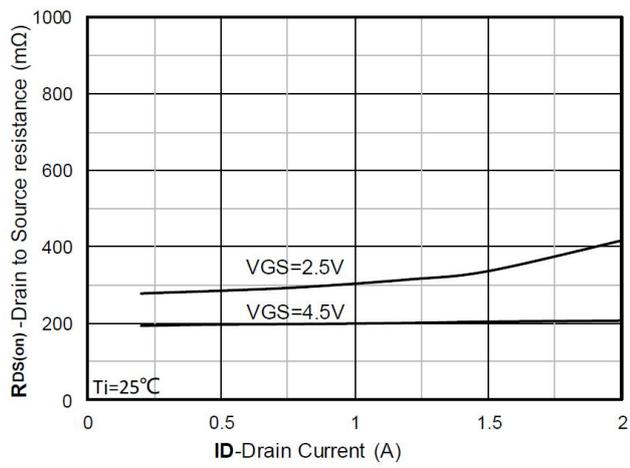
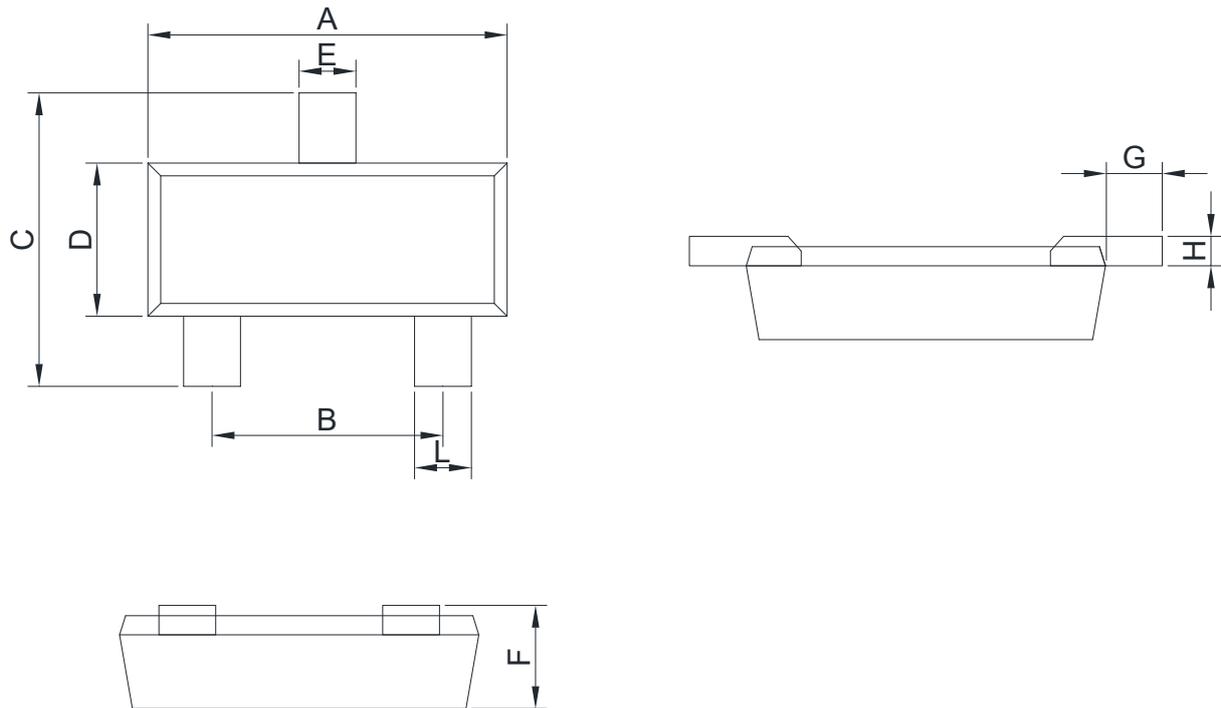


Figure7. $R_{DS(on)}$ VS Drain Current

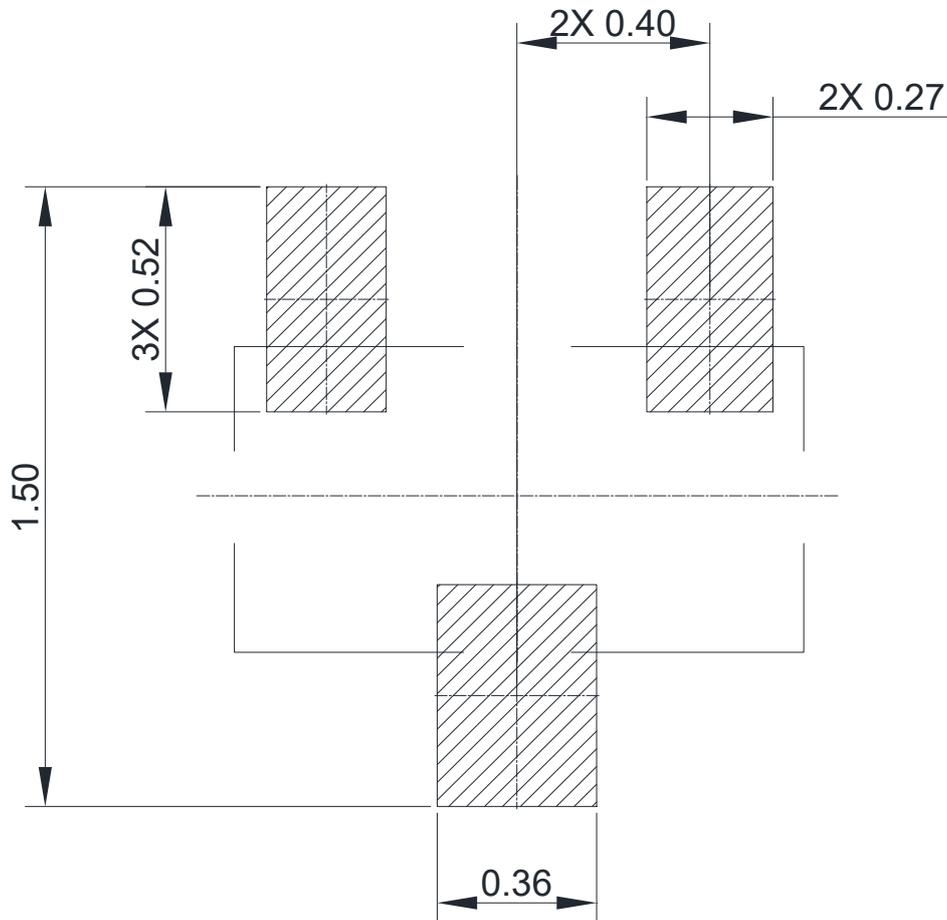
8. Dimension (SOT-723)

POD(Z)



Dimensions in Millimeters					
Symbol	Min.	Max.	Symbol	Min.	Max.
A	1.10	1.30	F	0.40	0.50
B	0.80TYP		G	0.10	0.30
C	1.10	1.30	H	0.06	0.16
D	0.70	0.90	L	0.15	0.25
E	0.15	0.35			

9. Recommended Soldering Footprint



DIMENSIONS: MILLIMETERS

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